



ON Semiconductor®

# FDS5690

## 60V N-Channel PowerTrench MOSFET

### General Description

This N-Channel MOSFET is produced using ON Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance.

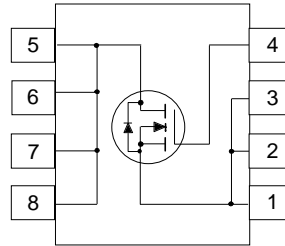
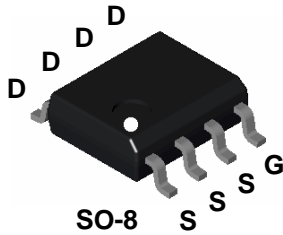
These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

### Applications

- DC/DC converter
- Motor drives

### Features

- 7 A, 60 V.  $R_{DS(on)} = 0.028 \Omega @ V_{GS} = 10 \text{ V}$   
 $R_{DS(on)} = 0.033 \Omega @ V_{GS} = 6 \text{ V}$ .
- Low gate charge (23nC typical).
- Fast switching speed.
- High performance trench technology for extremely low  $R_{DS(on)}$ .
- High power and current handling capability.



### Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage	60	V
V <sub>GSS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current - Continuous (Note 1a)	7	A
		50	
P <sub>D</sub>	Power Dissipation for Single Operation (Note 1a)	2.5	W
		1.2 (Note 1b)	
		1 (Note 1c)	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

### Thermal Characteristics

R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	°C/W
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case (Note 1)	25	°C/W

### Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDS5690	FDS5690	13"	12mm	2500 units

## DMOS Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	60			V
$\frac{\Delta BV_{DSS}}{\Delta T_j}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		57		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

### On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2	2.5	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_j}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-5.9		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 7\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 7\text{ A}, T_J = 125^\circ\text{C}$ $V_{GS} = 6\text{ V}, I_D = 6.5\text{ A}$		0.022 0.037 0.025	0.028 0.050 0.033	$\Omega$
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	25			A
$g_{FS}$	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 7\text{ A}$		24		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		1107		pF
$C_{oss}$	Output Capacitance			149		pF
$C_{rss}$	Reverse Transfer Capacitance			72		pF

### Switching Characteristics (Note 2)

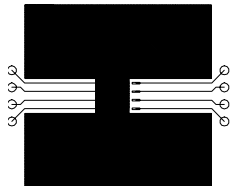
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 30\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$		10	18	ns
$t_r$	Turn-On Rise Time			9	18	ns
$t_{d(off)}$	Turn-Off Delay Time			24	39	ns
$t_f$	Turn-Off Fall Time			10	18	ns
$Q_g$	Total Gate Charge	$V_{DS} = 30\text{ V}, I_D = 7\text{ A},$ $V_{GS} = 10\text{ V},$		23	32	nC
$Q_{gs}$	Gate-Source Charge			4		nC
$Q_{gd}$	Gate-Drain Charge			6.8		nC

### Drain-Source Diode Characteristics and Maximum Ratings

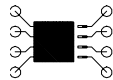
$I_S$	Maximum Continuous Drain-Source Diode Forward Current			2.1		A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 2.1\text{ A}$ (Note 2)		0.75	1.2	V

#### Notes:

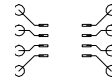
- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta JA}$  is determined by the user's board design.



a)  $50^\circ\text{C/W}$  when mounted on a  $0.5\text{ in}^2$  pad of 2 oz. copper.



b)  $105^\circ\text{C/W}$  when mounted on a  $0.02\text{ in}^2$  pad of 2 oz. copper.

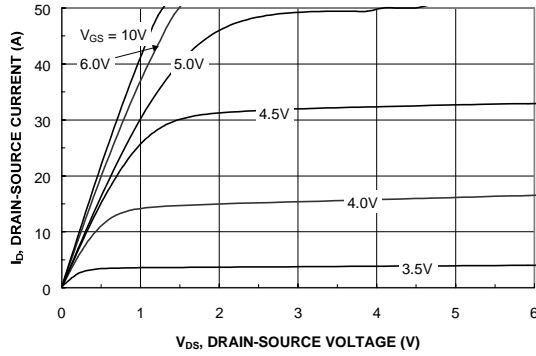


c)  $125^\circ\text{C/W}$  when mounted on a  $0.003\text{ in}^2$  pad of 2 oz. copper.

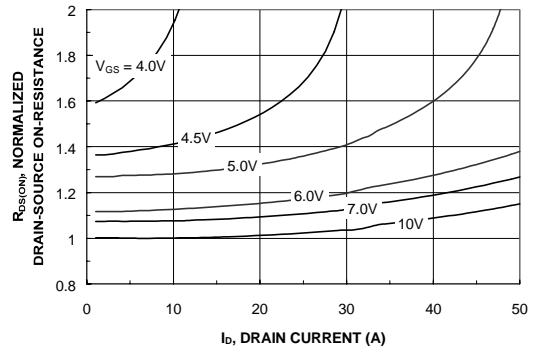
Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

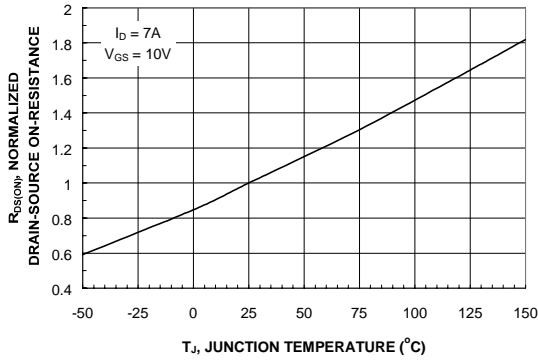
## Typical Characteristics



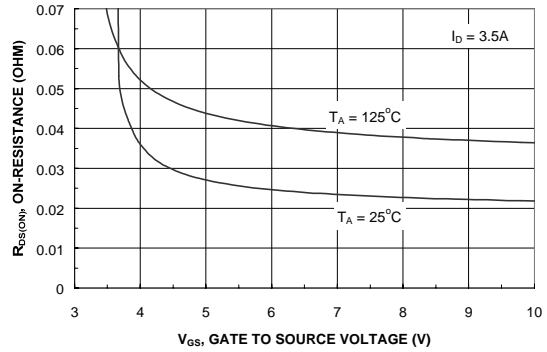
**Figure 1. On-Region Characteristics.**



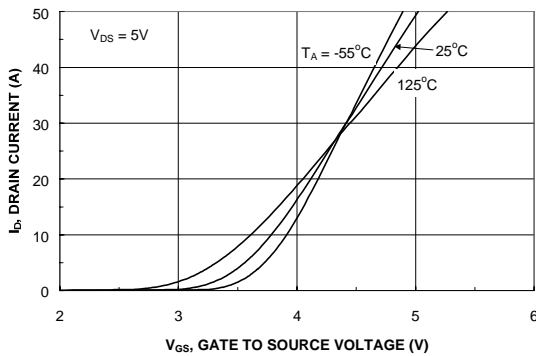
**Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.**



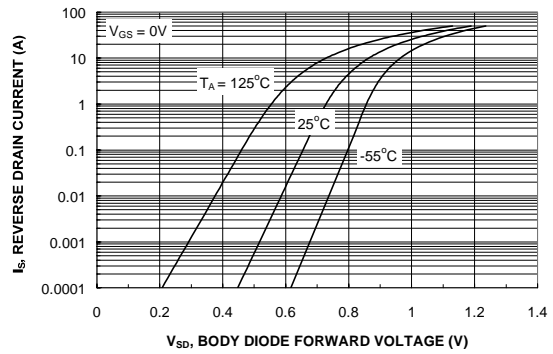
**Figure 3. On-Resistance Variation with Temperature.**



**Figure 4. On-Resistance Variation with Gate-to-Source Voltage.**

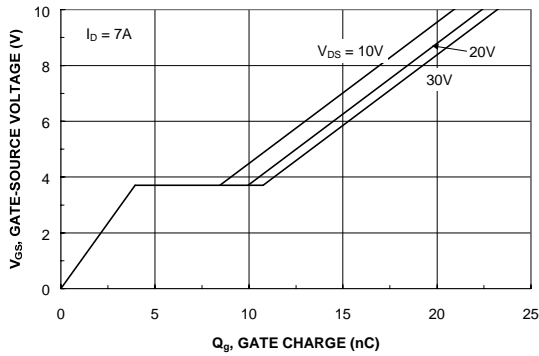


**Figure 5. Transfer Characteristics.**

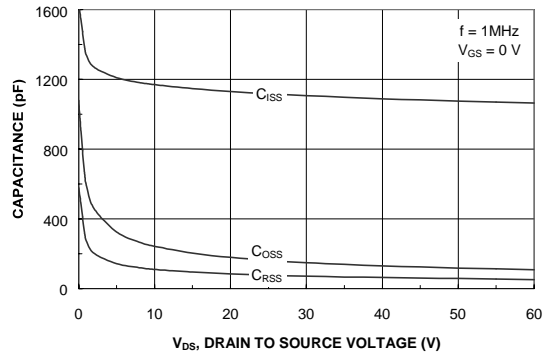


**Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.**

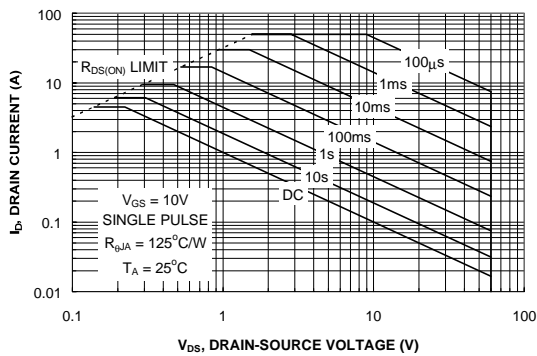
### Typical Characteristics (continued)



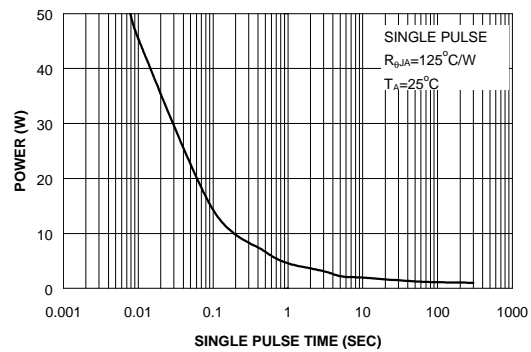
**Figure 7. Gate Charge Characteristics.**



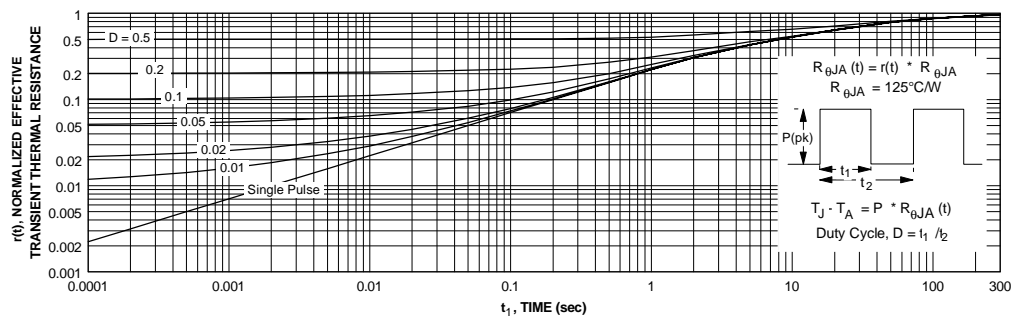
**Figure 8. Capacitance Characteristics.**



**Figure 9. Maximum Safe Operating Area.**



**Figure 10. Single Pulse Maximum Power Dissipation.**



**Figure 11. Transient Thermal Response Curve.**

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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